SUPPORTING INFORMATION

Semitransparent all-oxide ultraviolet light-emitting diodes based

on ZnO/NiO-core/shell nanowires

Zhi-Feng Shi,^a Ting-Ting Xu,^a Di Wu,^a Yuan-Tao Zhang,^b Bao-Lin Zhang,^b Yong-Tao Tian,^a Xin-Jian Li^{*a} and Guo-Tong Du^{*b}

^aDepartment of Physics and Laboratory of Material Physics, Zhengzhou University, Zhengzhou 450052, China

^bState Key Laboratory on Integrated Optoelectronics, College of Electronic Science and Engineering, Jilin University, Qianjin Street 2699, Changchun 130012, China

^{a)}Author to whom correspondence should be addressed. Electronic mail: <u>lixj@zzu.edu.cn</u>, <u>laserlab@jlu.edu.cn</u>

Ohmic contact behaviors of ITO and In electrodes on p-NiO and n-ZnO

Figure S1 shows the I-V characteristics of p-NiO and n-ZnO layers in contact with ITO and In electrodes, respectively. The Ohmic contact behaviors are confirmed by the fairly linear I-V dependencies.

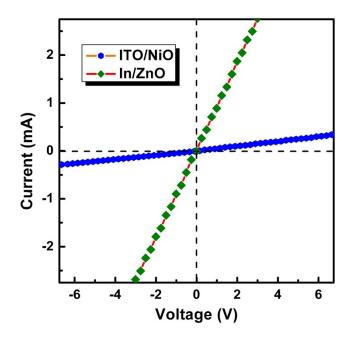


Figure S1. Ohmic contact behaviors of ITO and In electrodes on p-NiO and n-ZnO, respectively.